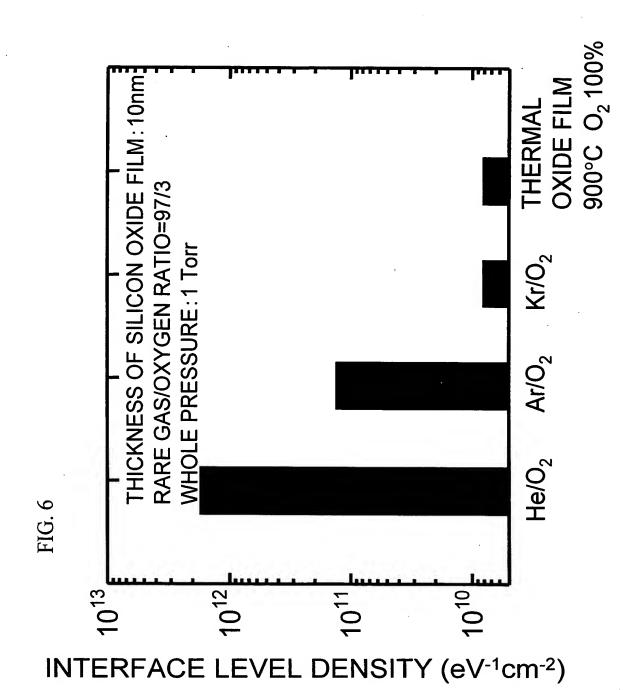
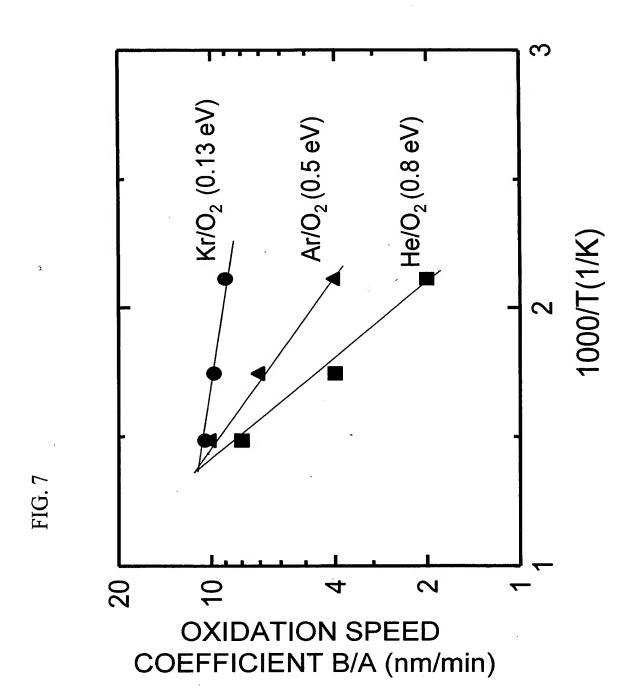
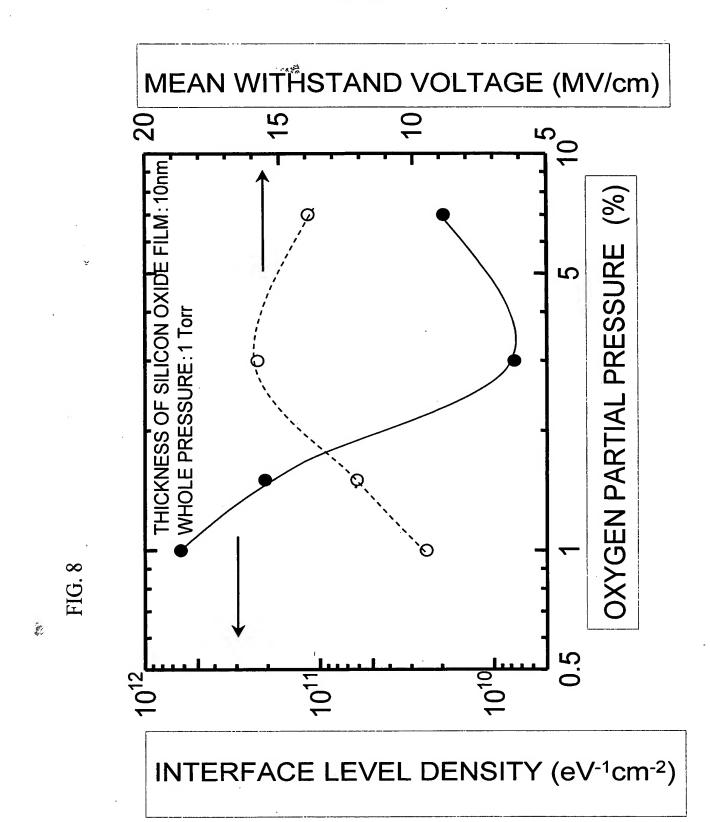


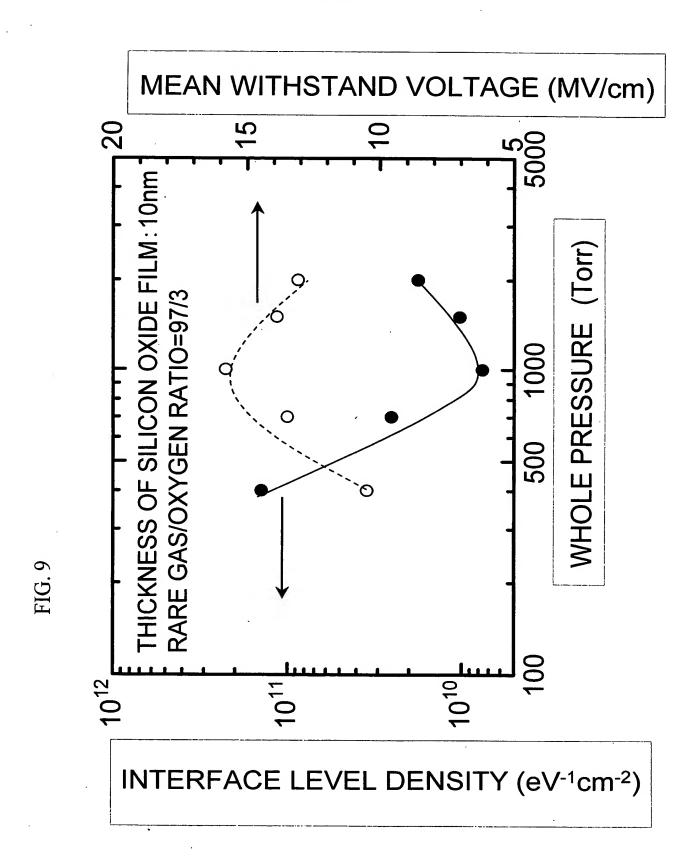
O/Si RATIO IN SILICON OXIDE FILM

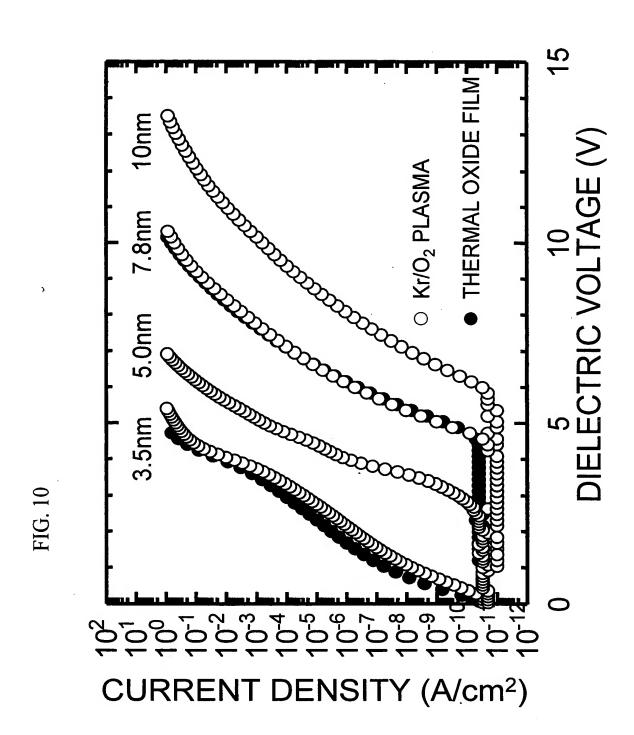


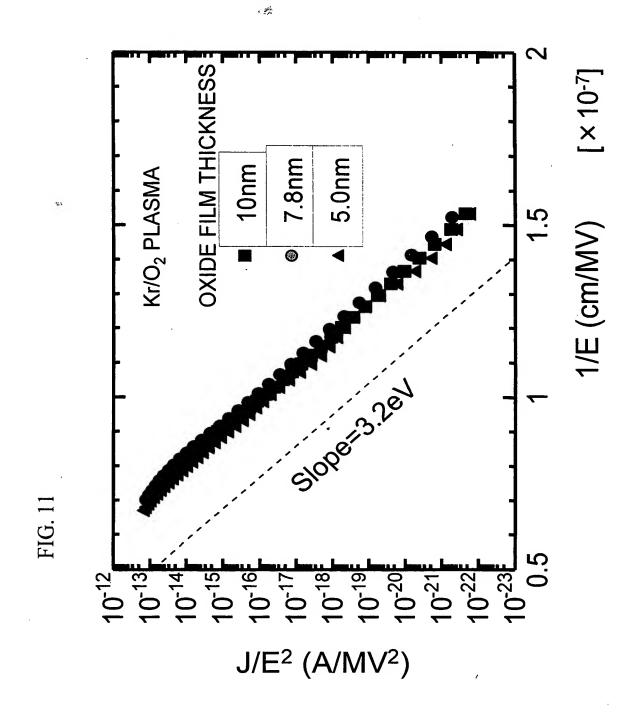


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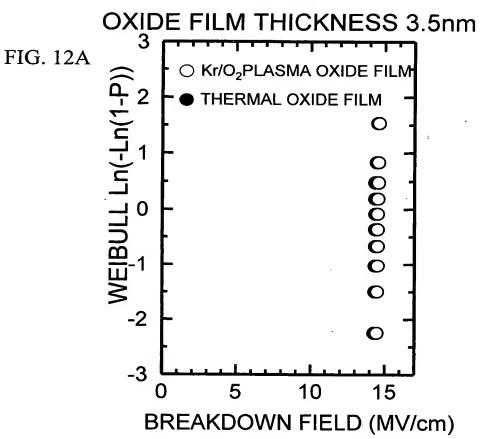




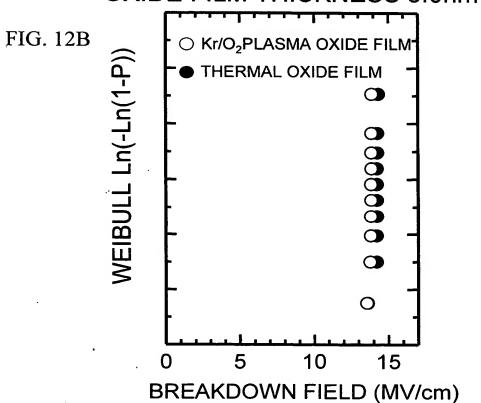


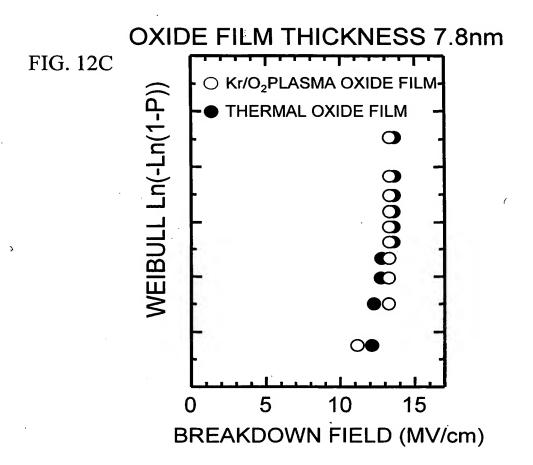






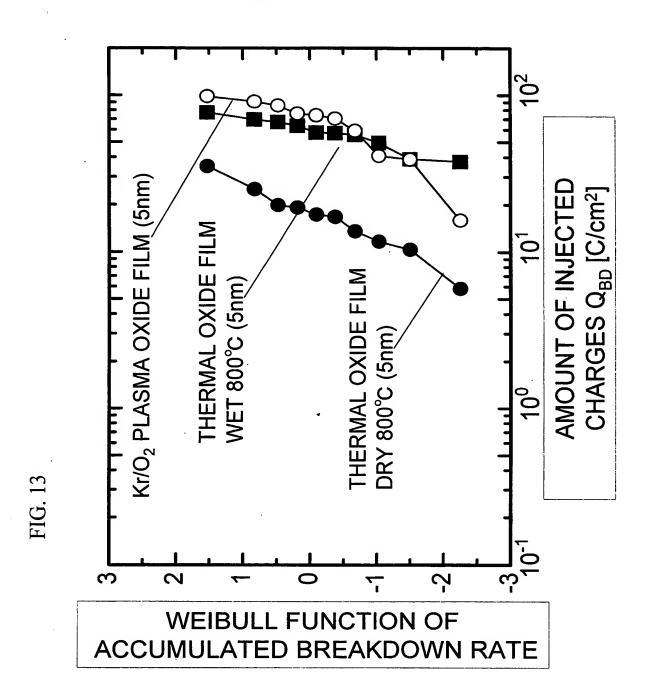


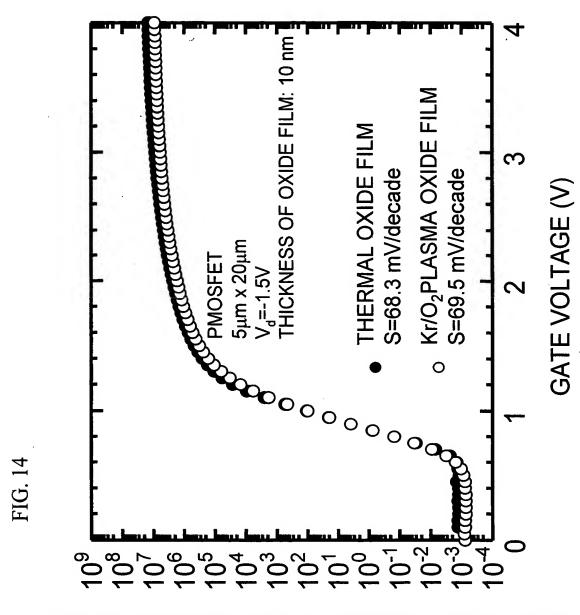




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DRAIN CURRENT/GATE CAPACITANCE (A/F)

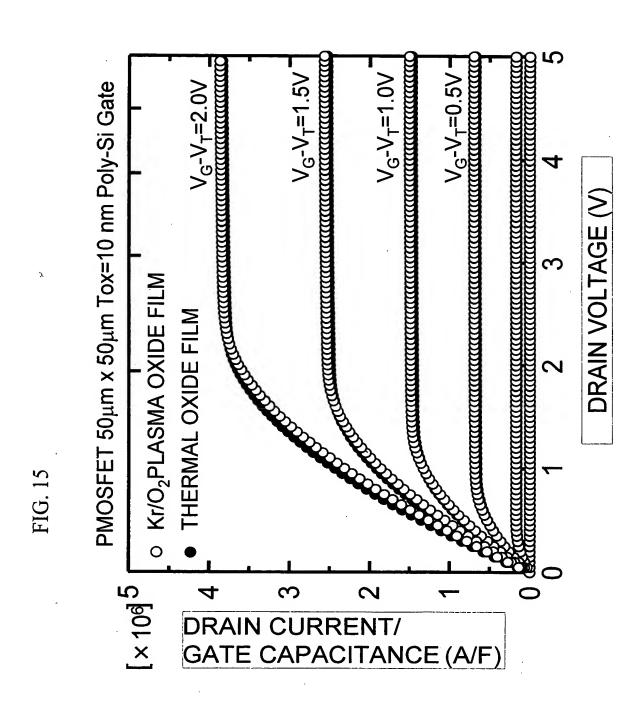


FIG. 16A

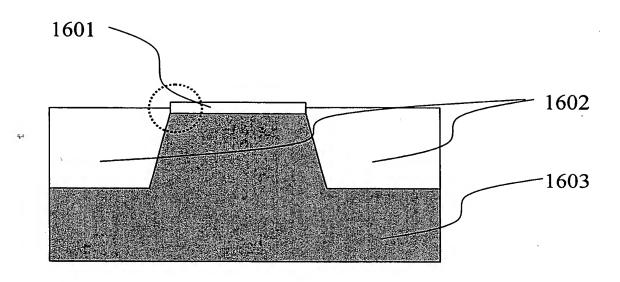
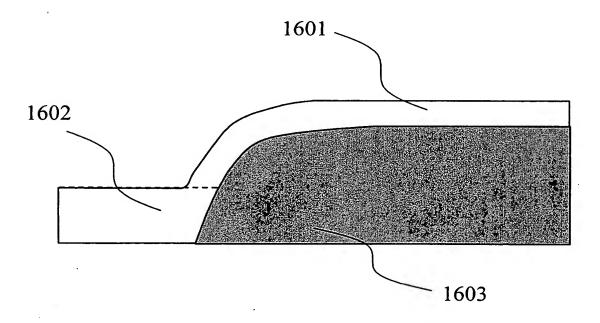
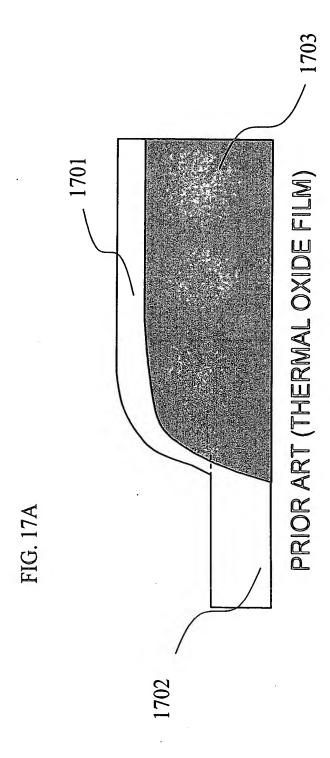
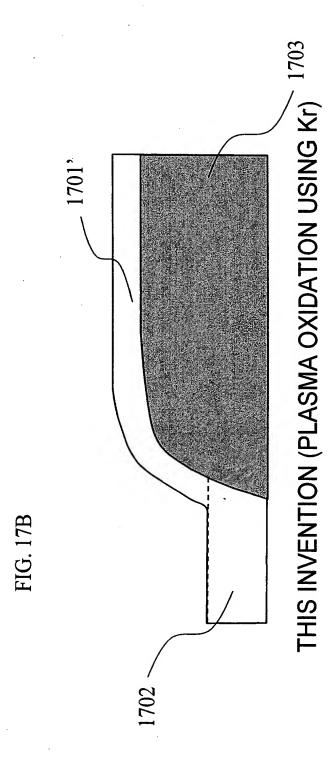


FIG. 16B

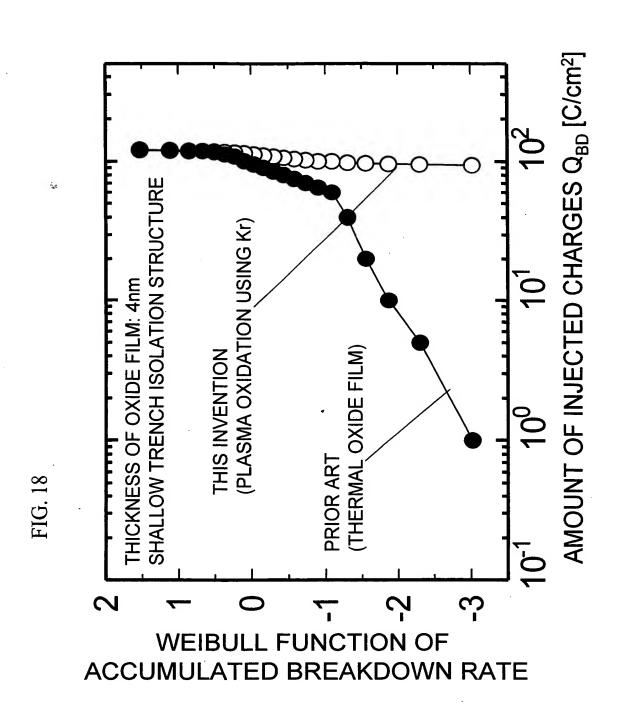


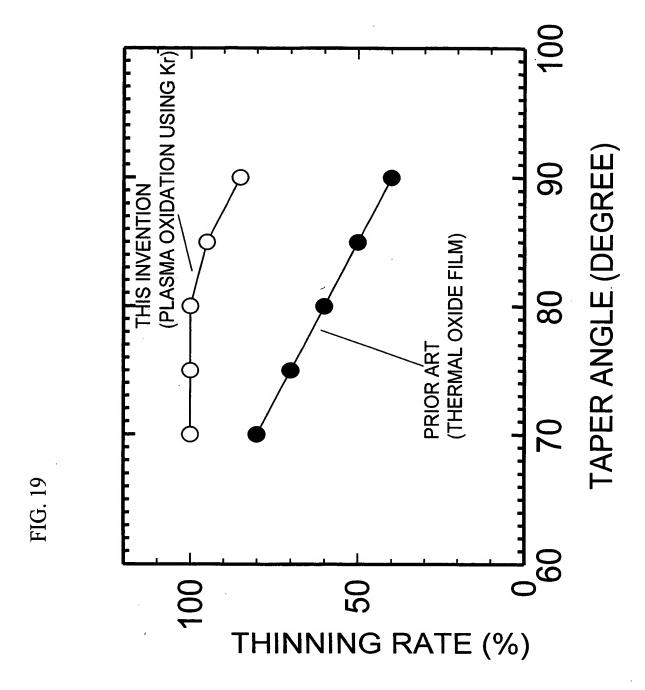


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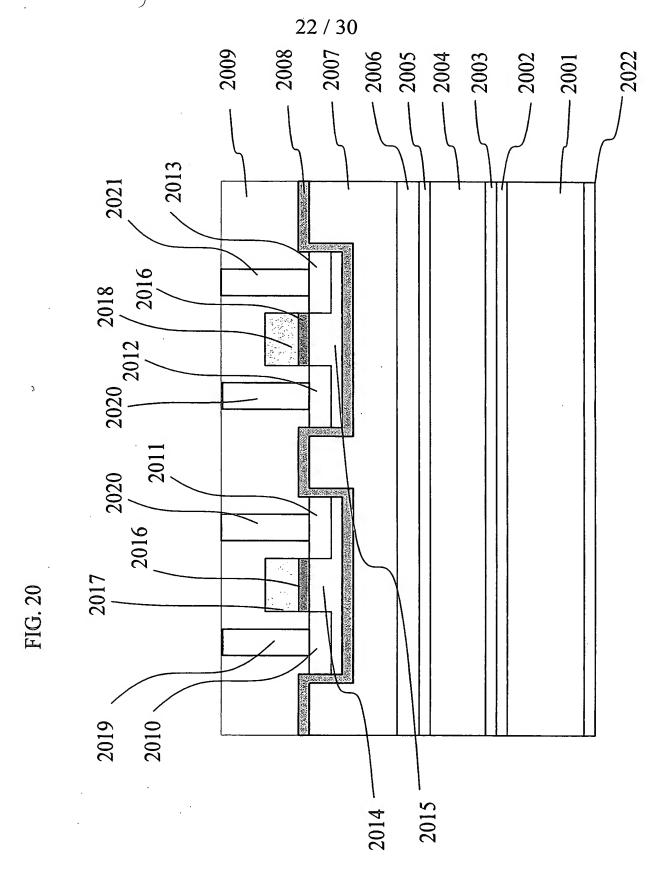


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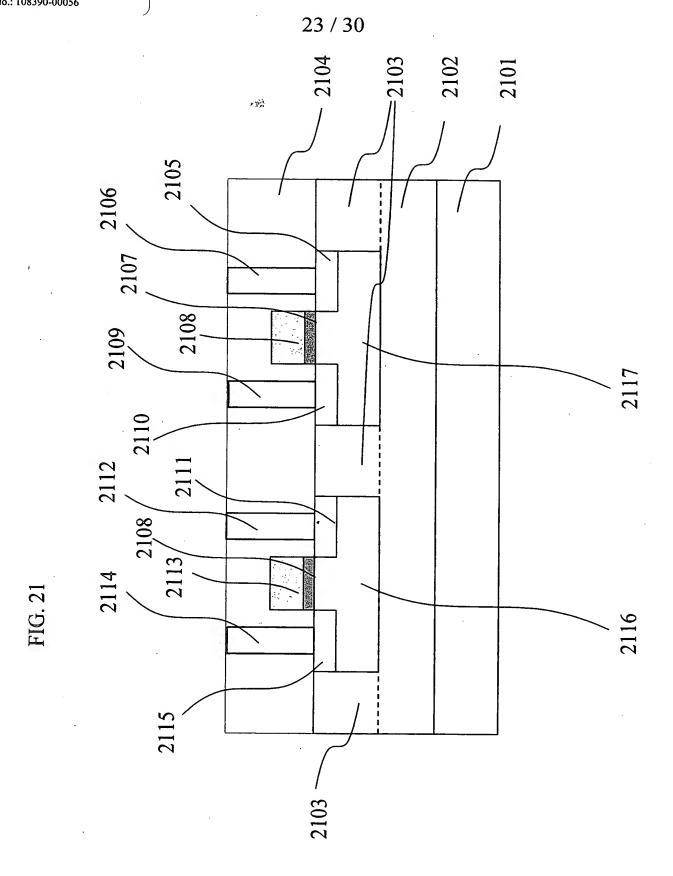


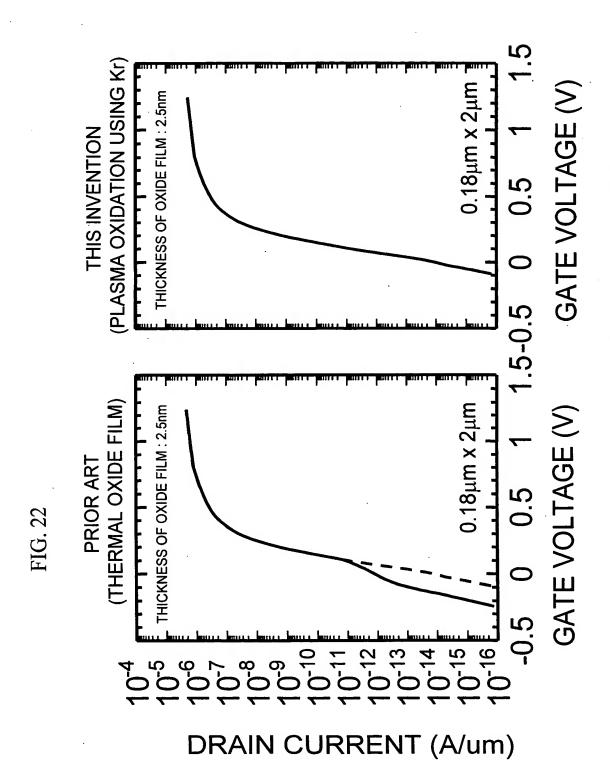


Title: DEVICE HAVING A SILICION OXIDE FILM
CONTAINING KRYPTON
Inventor's Name: Tadahiro OHMI
Divisional of Application No.: 09/787,435
Docket No.: 108390-00056

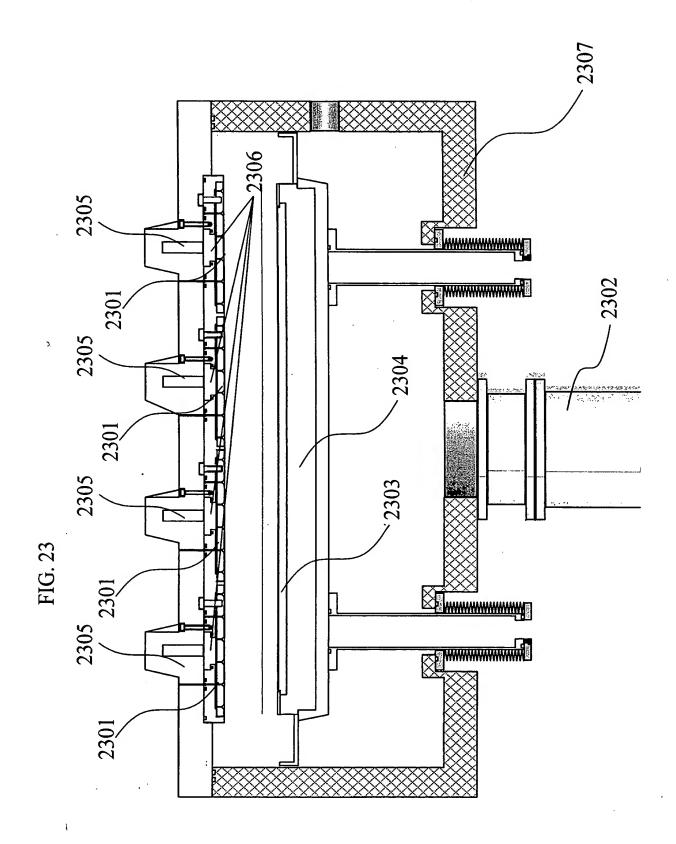


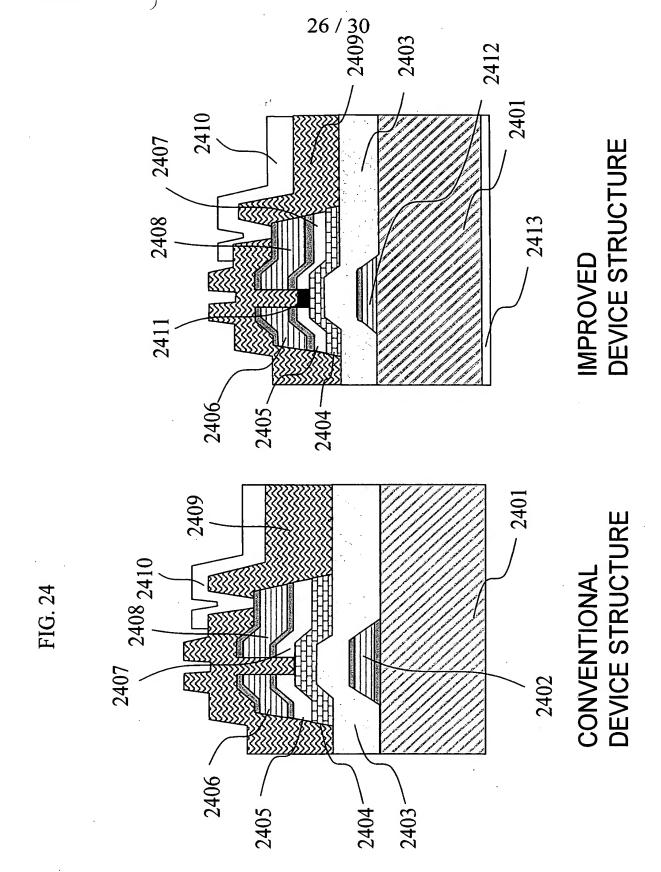
Title: DEVICE HAVING A SILICION OXIDE FILM
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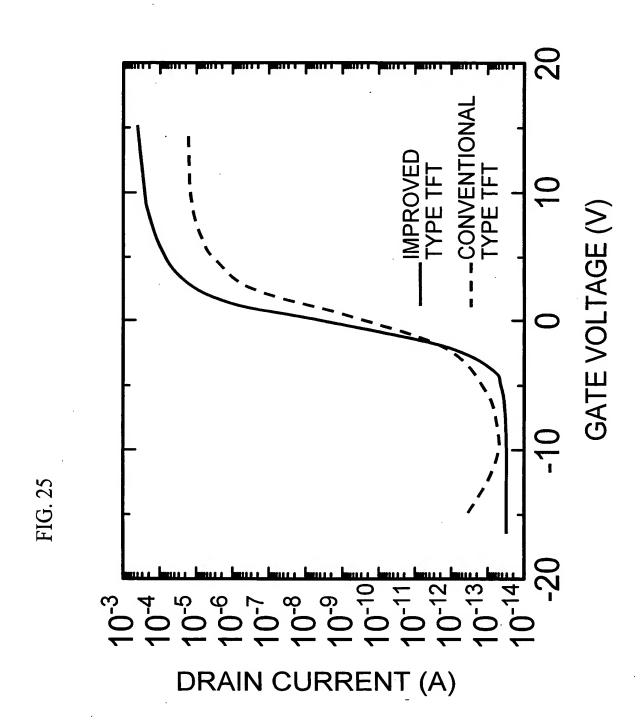




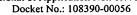
THICKNESS OF OXIDE FILM: 2.5nm

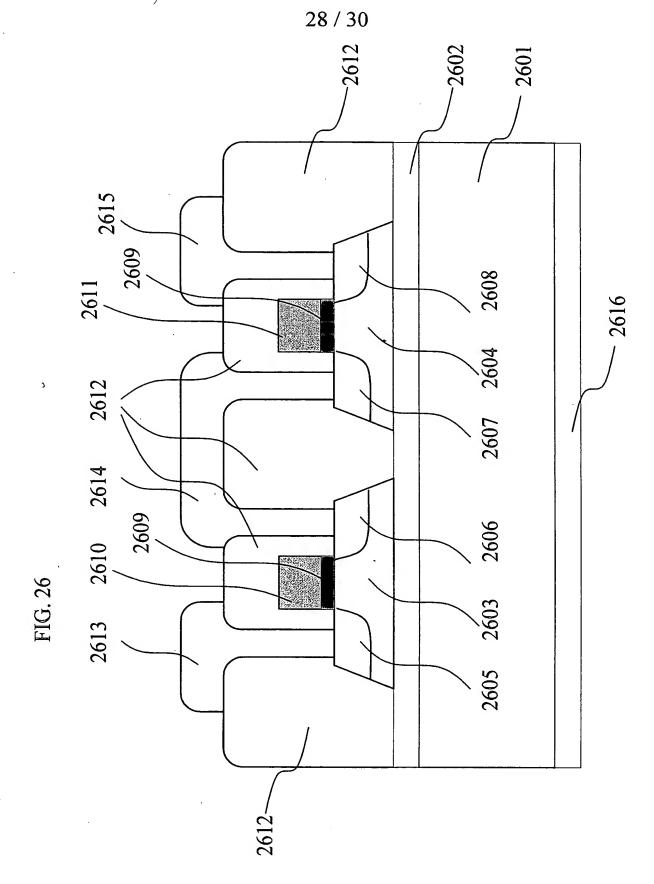






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